

IN THE CLAIMS

Please amend the claims as follows:

Claims 1-7 (Canceled).

Claim 8 (New): A method for transferring an electrically active thin film from an initial substrate to a target substrate, comprising:

ion implantation through one face of the initial substrate to create a buried, embrittled film at a determined depth in relation to the implanted face of the initial substrate, a thin film thus being delimited between the implanted face and the buried face;

fastening the implanted face of the initial substrate with a face of the target substrate;

separating the thin film from a remainder of the initial substrate at a level of the buried film; and

thinning down the thin film transferred on the target substrate;

wherein implantation dosage, energy and current are chosen, during the ion implantation, so that concentration of implantation defects is less than a determined threshold, resulting in, within the thinned down thin film, a number of acceptor defects that is compatible with desired electrical properties of the thin film.

Claim 9 (New): A method according to claim 8, wherein the ion implantation includes implanting ions chosen from among the following species: hydrogen and rare gases.

Claim 10 (New): A method according to claim 8, wherein the fastening includes a bonding chosen from bonding by molecular adhesion via intermediate films or without intermediate films, bonding by reaction, metallic bonding, brazing or bonding by species diffusion.

Claim 11 (New): A method according to claim 8, further comprising healing annealing of the implantation defects on the thin film.

Claim 12 (New): A method according to claim 11, wherein the healing annealing is carried out before the thinning down the thin film.

Claim 13 (New): A method according to claim 11, wherein the healing annealing is carried out after the thinning down the thin film.

Claim 14 (New): Application of the method according to claim 8 to obtain a thin film of SiC, GaAs, GaN, diamond, or InP on a target substrate.